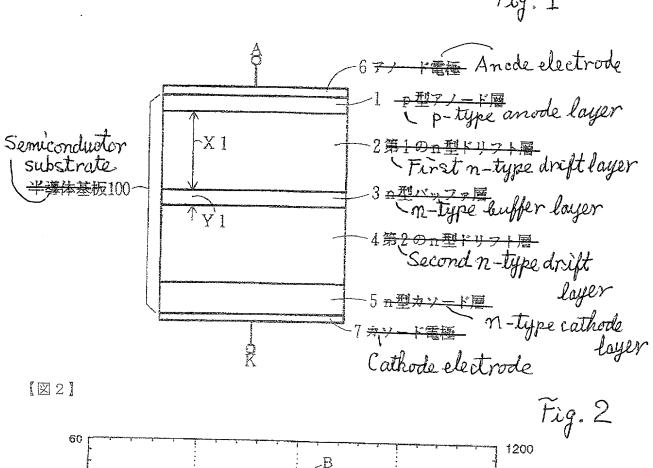
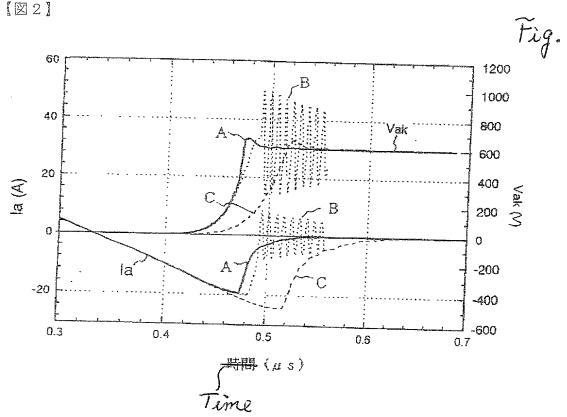
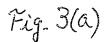


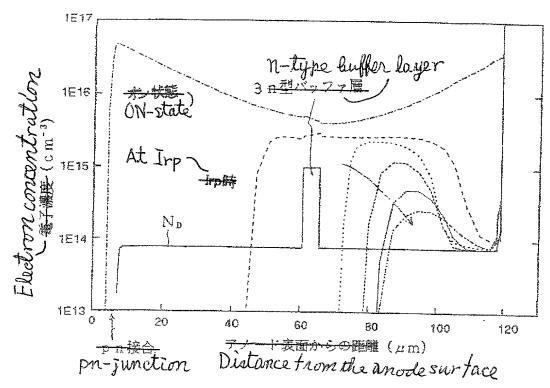
Fig. 1

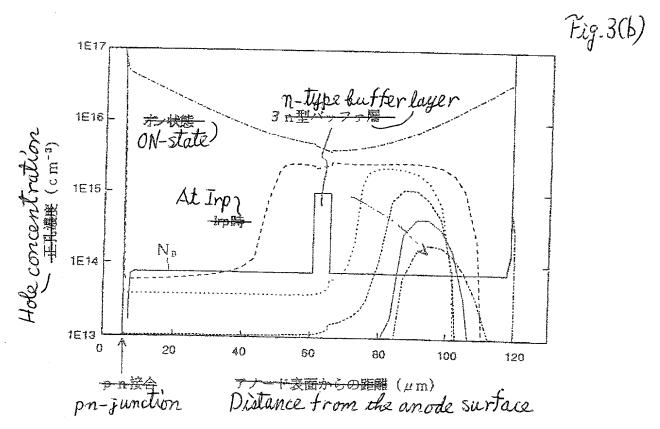




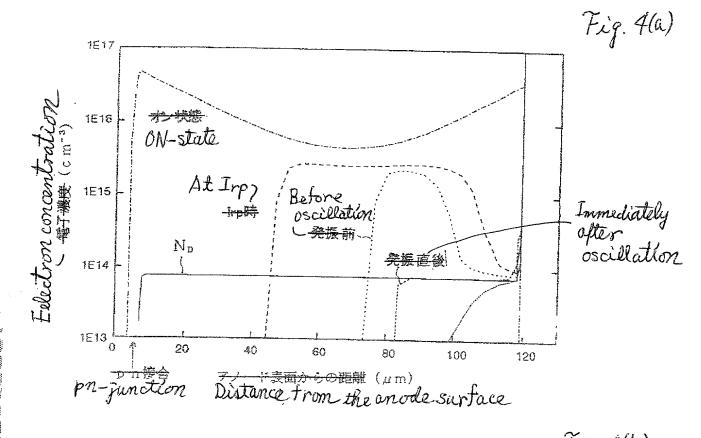


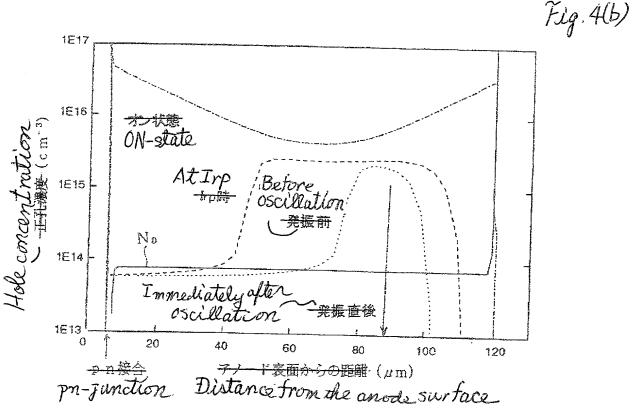


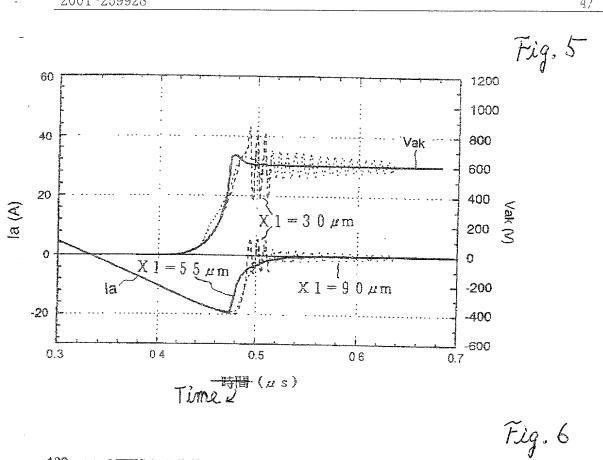


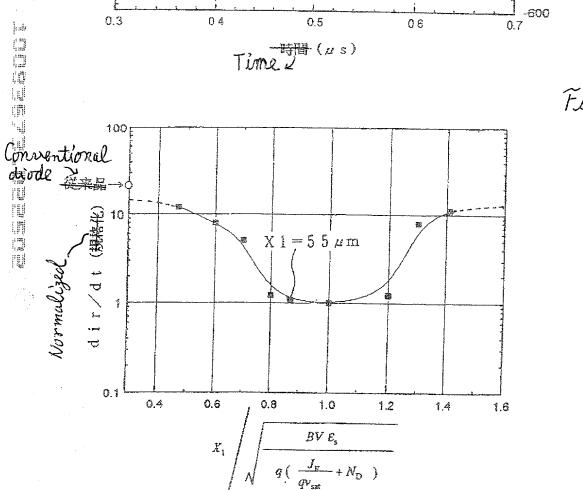


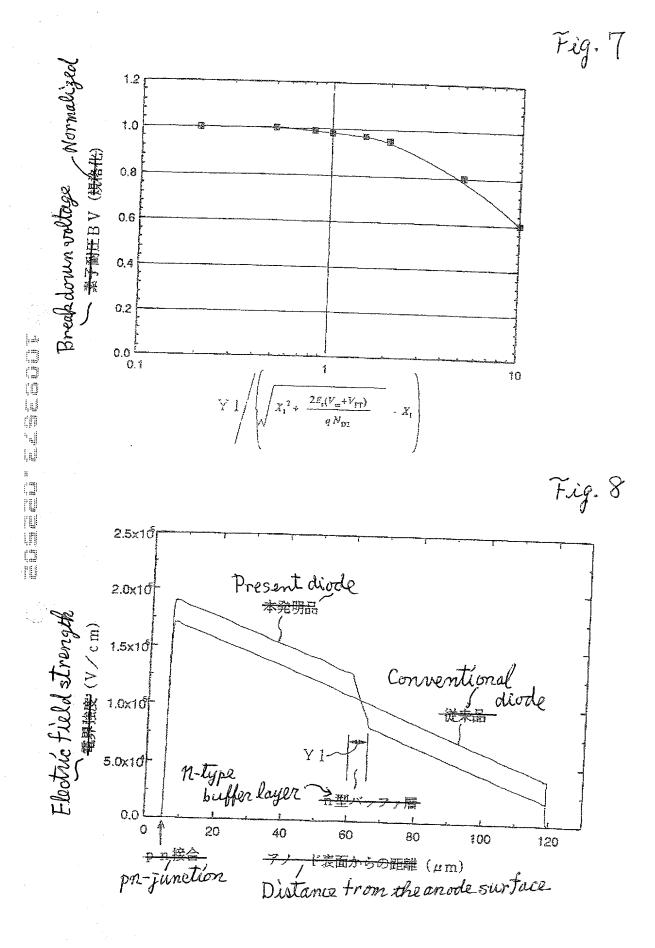














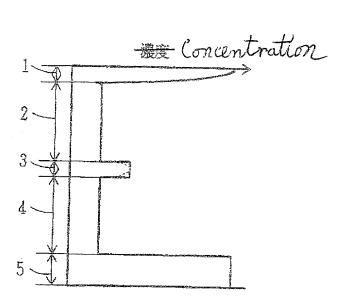
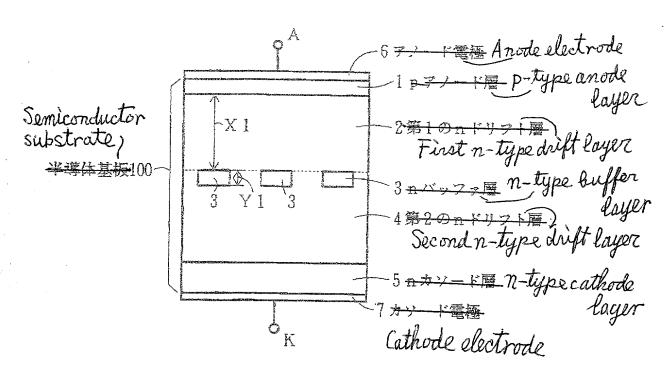
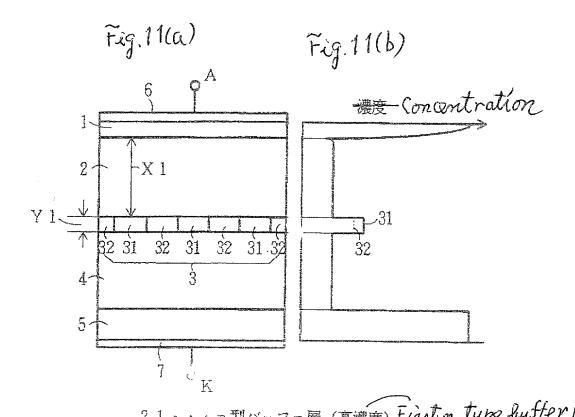
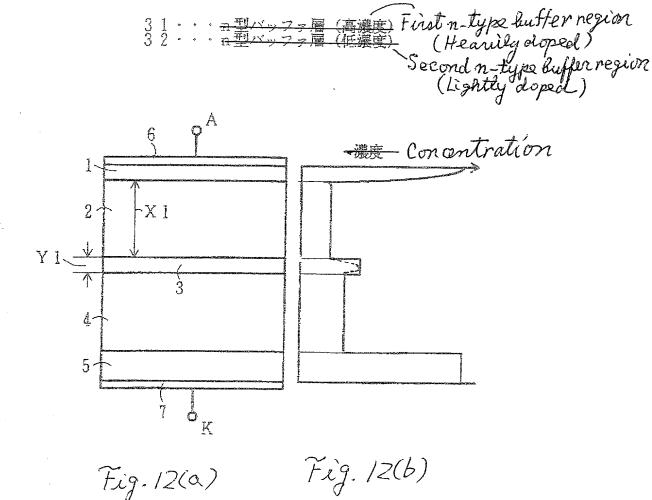


Fig. 9

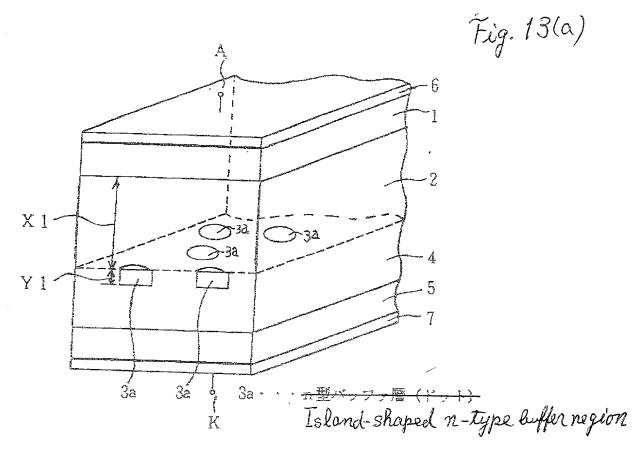
Fig. 10

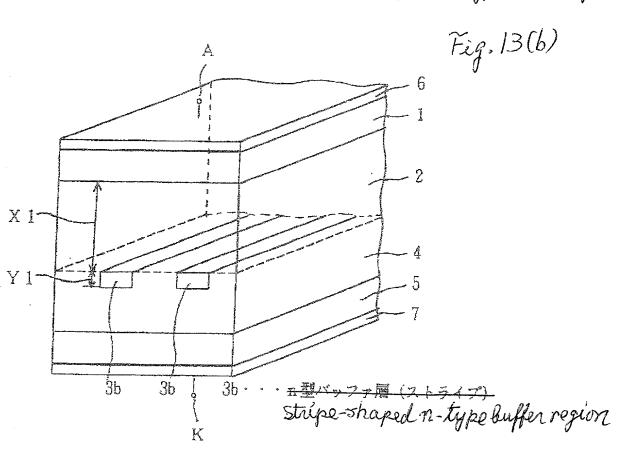


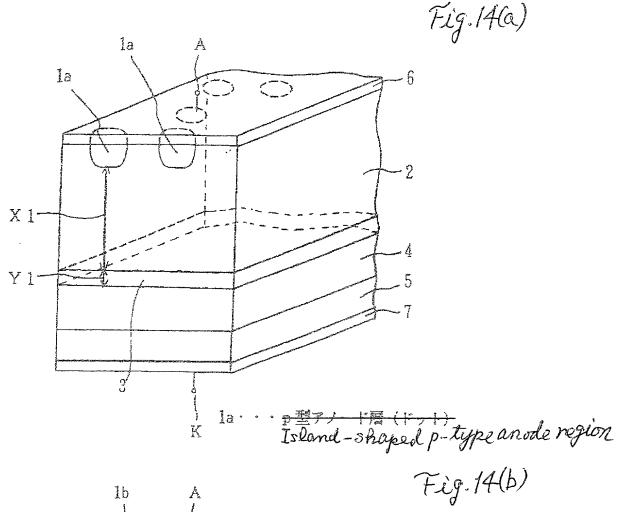


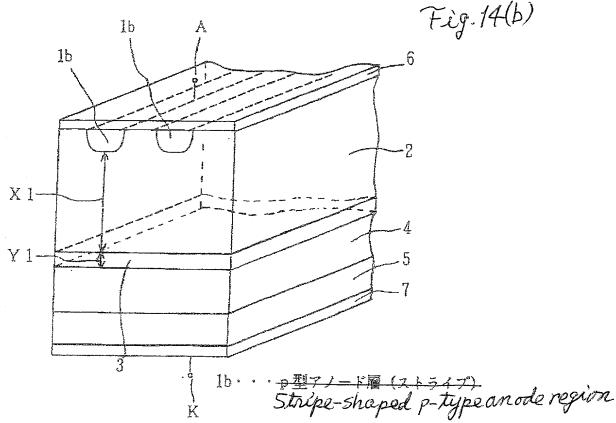


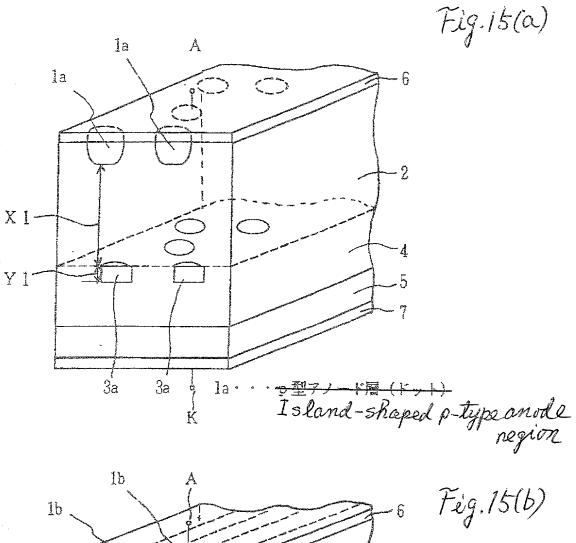
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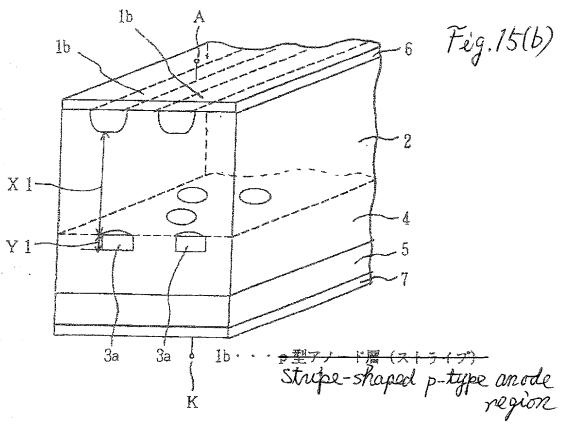














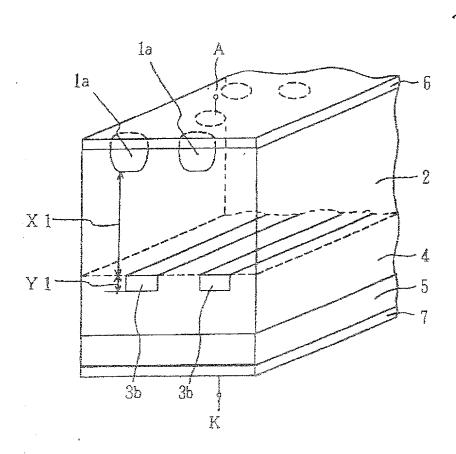


Fig. 16

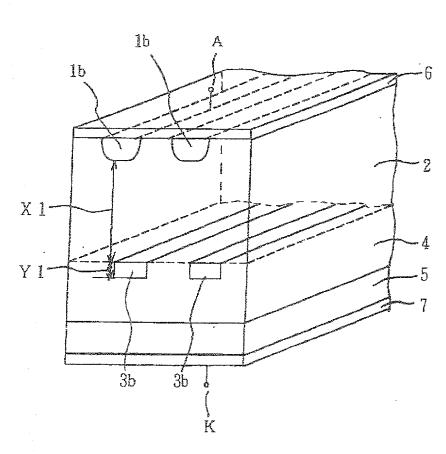
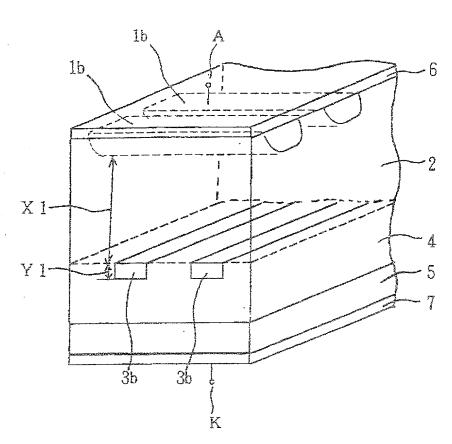
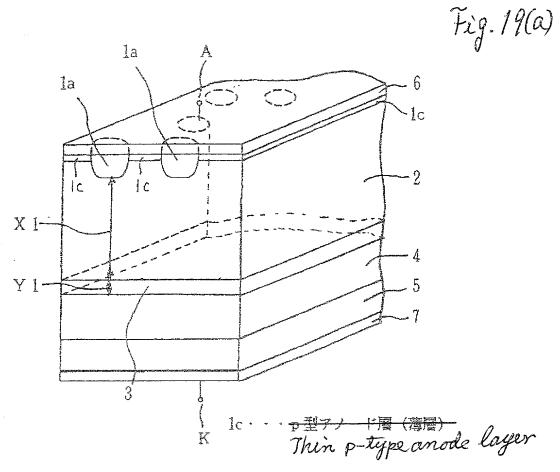


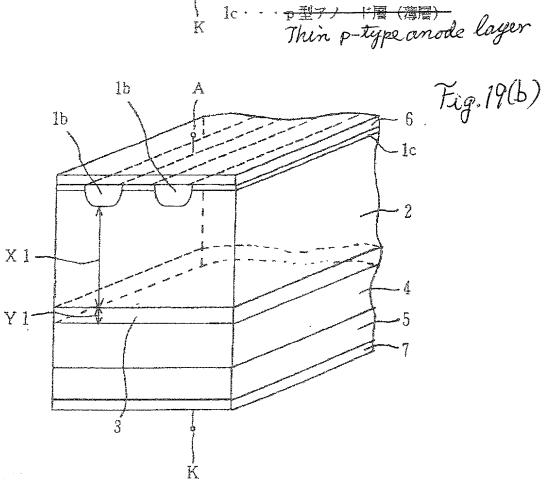
Fig.17

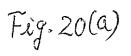
topacy negative

Fig. 18









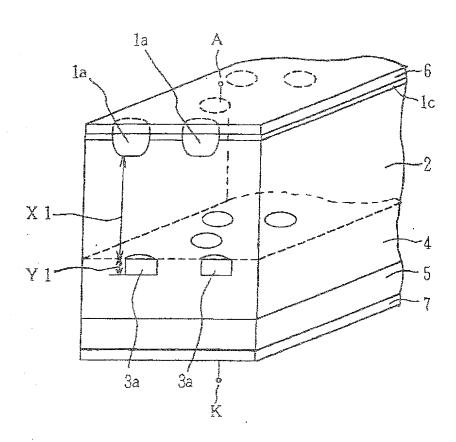
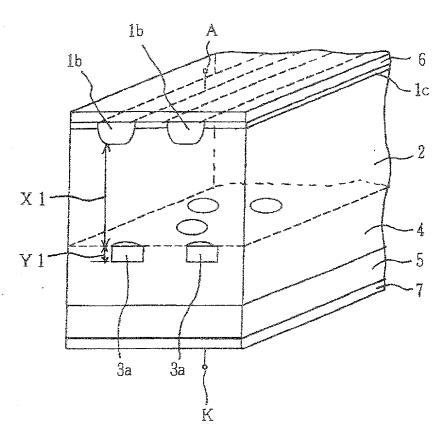


Fig. 20(b)



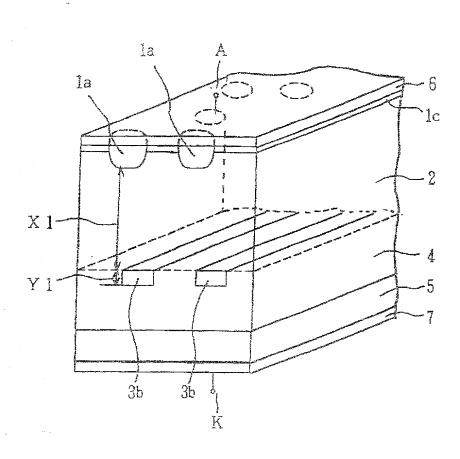


Fig. 21

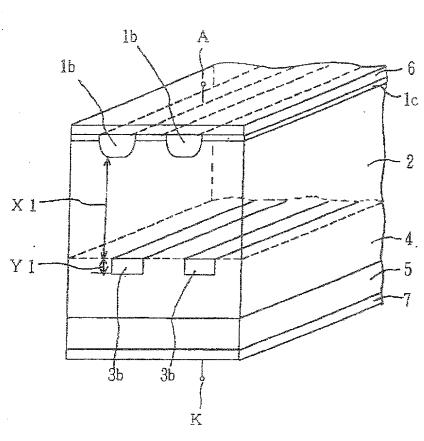


Fig. 22

Fig. 23

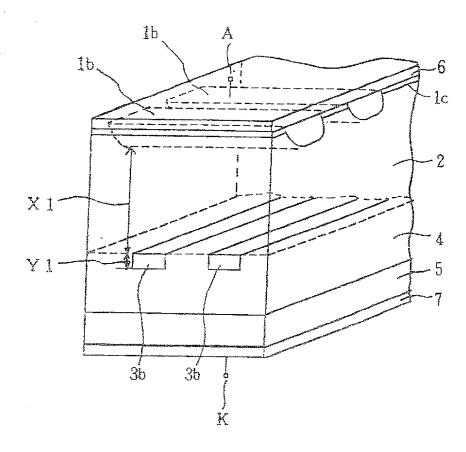
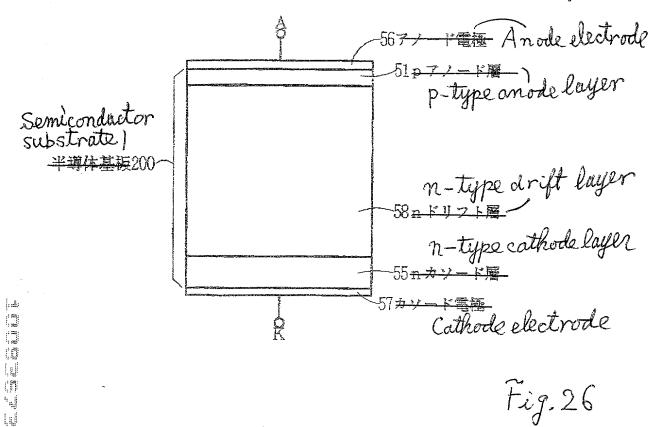
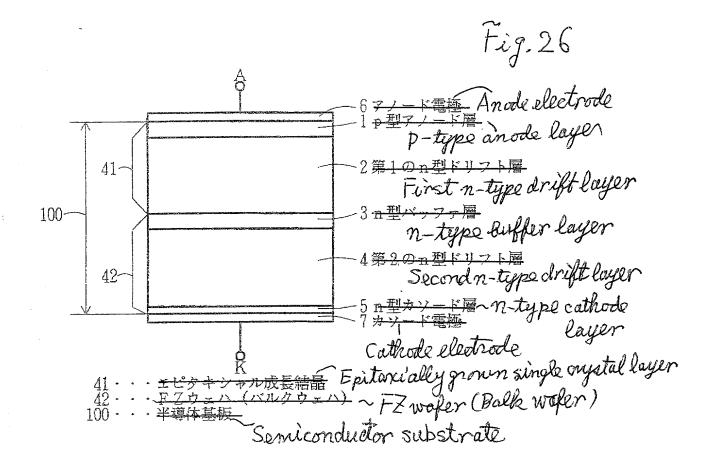


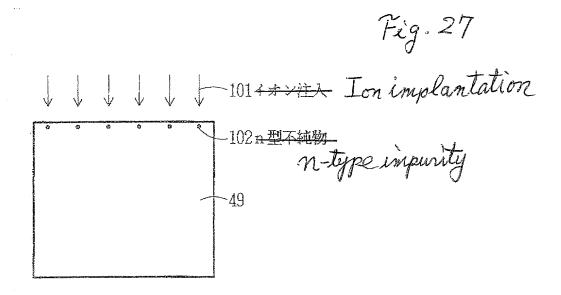
Fig. 24(a) Anode electrode 型フノード層 ) p-type anode layer Someconductor X. 1 substrate n-type buffer layer 半導体基長100 (athode electrode Fig. 24(b) Anode electrode IJ p-type anode layer Semiconductor X 1 半導体基板100 n-type huffer layer Y 1

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Cathode electrode







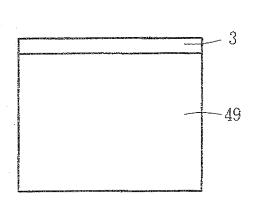


Fig-28

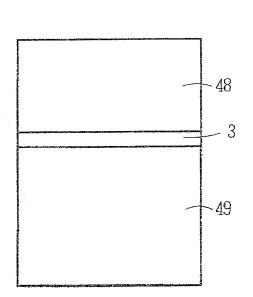
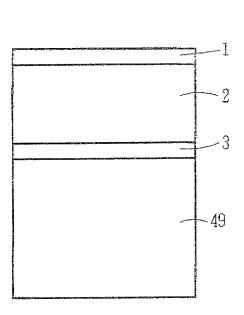


Fig. 29





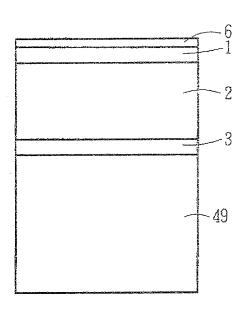
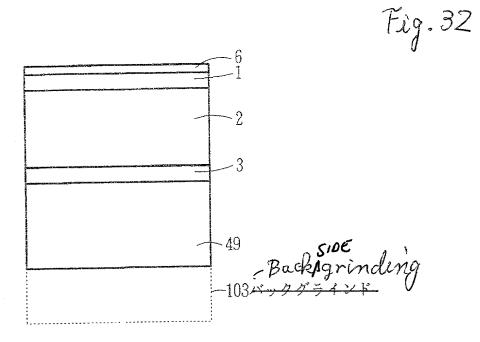
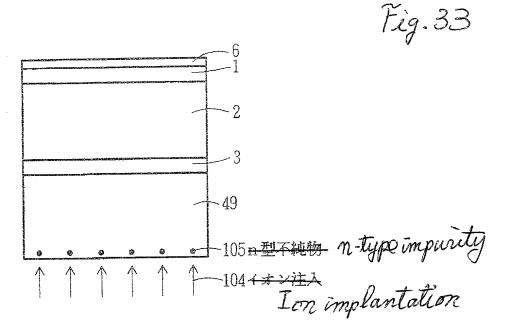
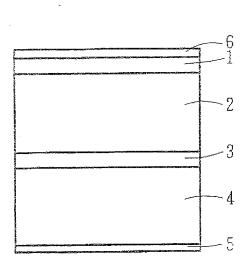


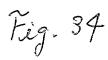
Fig. 31











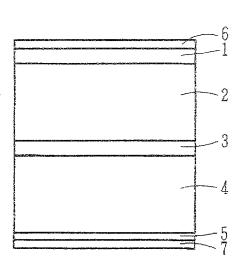


Fig. 35